

## X3-Class HiPerFET™ **Power MOSFET**

# IXFT170N25X3HV IXFH170N25X3 IXFK170N25X3

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode

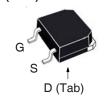


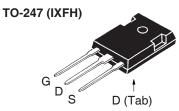
Symbol	Test Conditions	Maximum Ra	atings
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	250	V
V <sub>DGR</sub>	$T_{_{ m J}}$ = 25°C to 150°C, $R_{_{ m GS}}$ = 1M $\Omega$	250	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	170	A
I <sub>L(RMS)</sub>	External Lead Current Limit	160	Α
I <sub>DM</sub>	$\rm T_{_{\rm C}}$ = 25°C, Pulse Width Limited by $\rm T_{_{\rm JM}}$	400	А
I <sub>A</sub>	T <sub>c</sub> = 25°C	85	A
E <sub>AS</sub>	$T_{c} = 25^{\circ}C$	2.3	J
dv/dt	$I_{_{\mathrm{S}}} \leq I_{_{\mathrm{DM}}}, \ V_{_{\mathrm{DD}}} \leq V_{_{\mathrm{DSS}}}, \ T_{_{\mathrm{J}}} \leq 150^{\circ}\mathrm{C}$	20	V/ns
$P_{D}$	T <sub>c</sub> = 25°C	890	W
T <sub>J</sub>		-55 +150	°C
$T_{JM}$		150	°C
T <sub>stg</sub>		-55 +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C
T <sub>SOLD</sub>	1.6 mm (0.062in.) from Case for 10s	260	°C
$M_d$	Mounting Torque (TO-247 & TO-264)	1.13 / 10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247 TO-264	6 10	g g

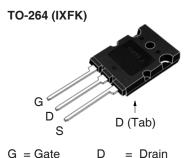
SymbolTest ConditionsCharacteristics $(T_J = 25^{\circ}C, Unless Otherwise Specified)$ Min.		cteristic Values Typ.   Max.			
BV <sub>DSS</sub>	$V_{GS} = 0V, I_D = 1mA$	250			V
$V_{\rm GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 4mA$	2.5		4.5	V
I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
DSS	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_{J} = 125$ °C			10 1	μA mA
R <sub>DS(on)</sub>	$V_{GS} = 10V, I_{D} = 0.5 \cdot I_{D25}, Note 1$		6.1	7.4	mΩ

250V 170A D25  $7.4m\Omega$  $\leq$  $\mathbf{R}_{\mathrm{DS(on)}}$ 

#### TO-268HV (IXFT)







#### **Features**

S = Source

• International Standard Packages

Tab = Drain

- Low  $R_{DS(ON)}$  and  $Q_G$  Avalanche Rated
- Low Package Inductance

#### **Advantages**

- High Power Density
- Easy to Mount
- Space Savings

#### **Applications**

- Switch-Mode and Resonant-Mode **Power Supplies**
- DC-DC Converters
- PFC Circuits
- · AC and DC Motor Drives
- Robotics and Servo Controls



Symbol Test Conditions Char		acteristic Values		
$(T_J = 25^{\circ}C, Unless Otherwise Specified)$ Min.		Тур.	Max	
g <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 60A, Note 1	66	110	S
$R_{Gi}$	Gate Input Resistance		1.3	Ω
C <sub>iss</sub>			13.5	nF
C <sub>oss</sub>	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		2.3	nF
C <sub>rss</sub>			1.6	pF
	Effective Output Capacitance			
$C_{o(er)}$	Energy related $\int V_{GS} = 0V$		800	pF
$\mathbf{C}_{o(tr)}$	Time related $\int V_{DS}^{GS} = 0.8 \cdot V_{DSS}$		3280	pF
t <sub>d(on)</sub>	Resistive Switching Times		18	ns
t, (	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		10	ns
t <sub>d(off)</sub>	$R_{\rm G} = 5\Omega$ (External)		62	ns
t <sub>f</sub>	$n_{\rm G} = 352$ (External)		7	ns
$Q_{g(on)}$			190	nC
Q <sub>gs</sub>	$V_{gs} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		55	nC
Q <sub>gd</sub>			45	nC
R <sub>thJC</sub>				0.14 °C/W
R <sub>thCS</sub>	TO-247		0.21	°C/W
	TO-264		0.15	°C/W

#### Source-Drain Diode

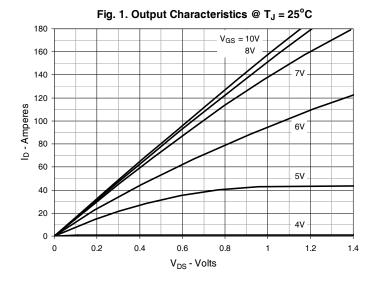
Symbol					
$(T_J = 25^{\circ}C, U)$	Jnless Otherwise Specified)	Min.	Тур.	Max	
Is	$V_{GS} = 0V$			170	Α
SM	Repetitive, pulse Width Limited by $\mathrm{T}_{_{\mathrm{JM}}}$			680	Α
V <sub>SD</sub>	$I_F = I_S$ , $V_{GS} = 0V$ , Note 1			1.4	V
$\left\{egin{array}{c} \mathbf{t}_{rr} & \\ \mathbf{Q}_{RM} & \\ \mathbf{I}_{RM} & \end{array} ight\}$	$I_F = 85A$ , -di/dt = 100A/ $\mu$ s $V_R = 100V$		140 770 11		ns nC A

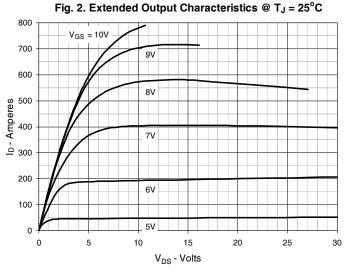
Note 1. Pulse test,  $t \le 300 \mu s$ , duty cycle,  $d \le 2\%$ .

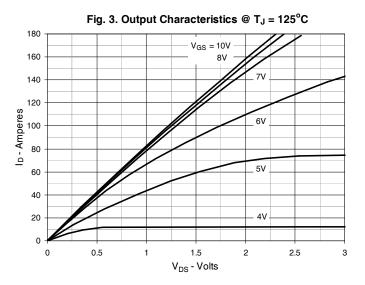
#### PRELIMINARY TECHNICAL INFORMATION

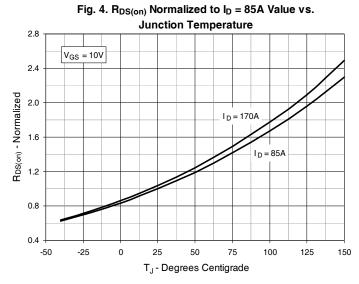
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

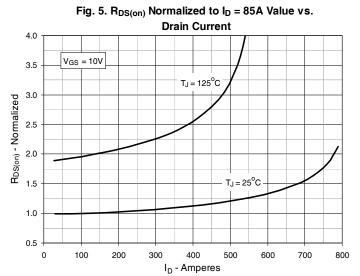


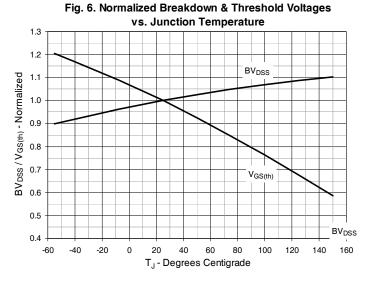




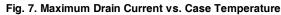












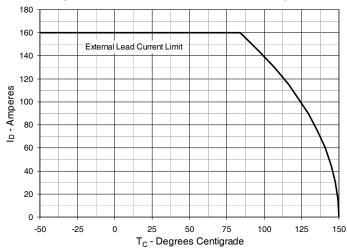


Fig. 8. Input Admittance

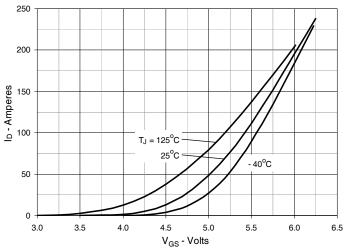


Fig. 9. Transconductance

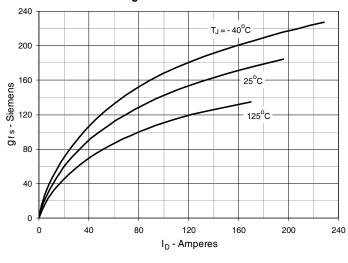


Fig. 10. Forward Voltage Drop of Intrinsic Diode

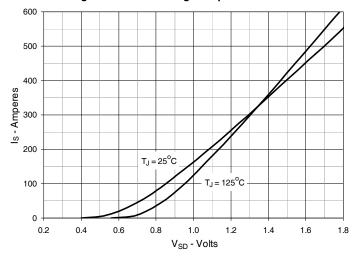


Fig. 11. Gate Charge

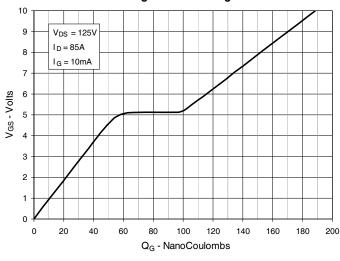
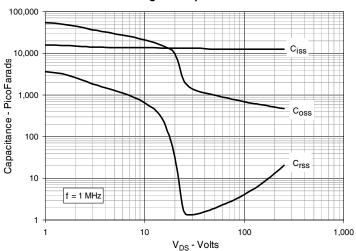
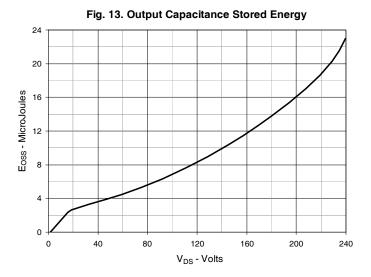


Fig. 12. Capacitance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.





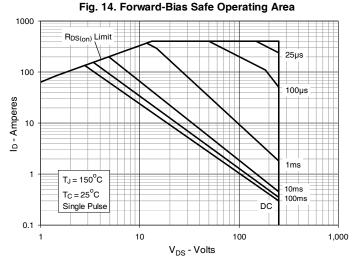
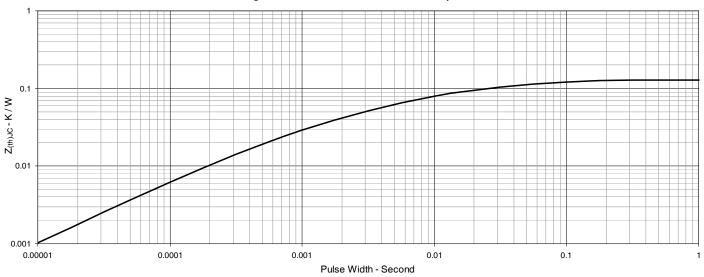
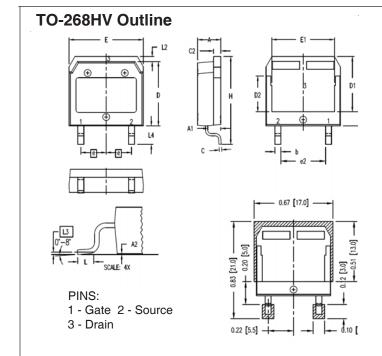


Fig. 15. Maximum Transient Thermal Impedance





### IXFT170N25X3HV IXFH170N25X3 IXFK170N25X3



SYM	INCHES		MILLIMETER		
31101	MIN	MAX	MIN	MAX	
Α	.193	.201	4.90	5.10	
Α1	.106	.114	2.70	2.90	
A2	.001	.010	0.02	0.25	
Ь	.045	.057	1.15	1.45	
С	.016	.026	0.40	0.65	
C2	.057	.063	1.45	1.60	
D	.543	.551	13.80	14.00	
D1	.465	.476	11.80	12.10	
D2	.295	.307	7.50	7.80	
D3	.114	.126	2.90	3.20	
E	.624	.632	15.85	16.05	
E1	.524	.535	13.30	13.60	
е	.215 BSC		5. <b>4</b> 5 BSC		
(e2)	.374	.386	9.50	9.80	
Н	.736	.752	18.70	19.10	
L	.067	.079	1.70	2.00	
L2	.039	.045	1.00	1.15	
L3	.010	BSC	0.25 BSC		
L4	.150	.161	3.80	<b>4</b> .10	

